

DFN2510-10 Plastic-Encapsulate ESD Protection Diodes

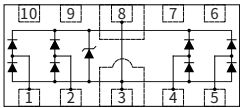
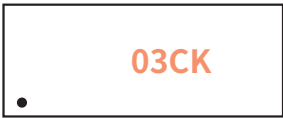
Features

- Low leakage current
- Low clamping voltage
- IEC 61000-4-2 (ESD Air): ±20kV
- IEC 61000-4-2 (ESD Contact): ±15kV
- IEC 61000-4-5 (Lightning 8/20μs): 7A

Applications

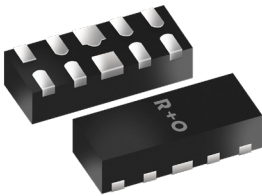
- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation, Digital Cameras
- Peripherals, Audio Players, Industrial Equipment

Function Diagram



Reverse Working Voltage
3.3V Max.
Low capacitance
0.5pF(Max.)

DFN2510-10

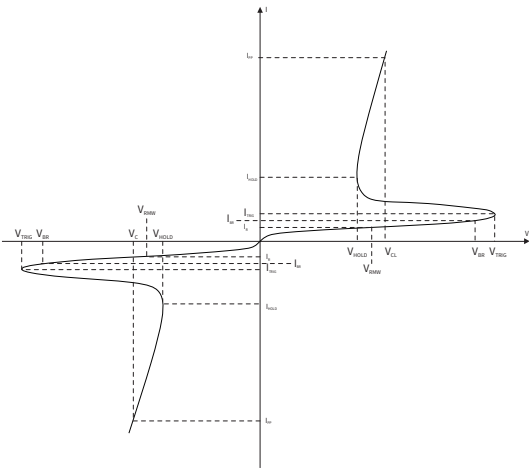


Maximum Ratings (Ta=25°C Unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
VESD	Electrostatic Discharge Voltage	ESD per IEC 61000-4-2(Air)	±20	KV
		ESD per IEC 61000-4-2(Contact)	±15	KV
P _{PP}	Peak Pulse Power	tp = 8/20 μs	35	W
I _{PP}	Rated Peak Pulse Current	tp = 8/20 μs	7.0	A
T _J	Operating JunctionTemperature Range	—	-40 to +125	°C
T _{STG}	Operating JunctionTemperature Range	—	-55 to +150	°C

Electrical Parameter

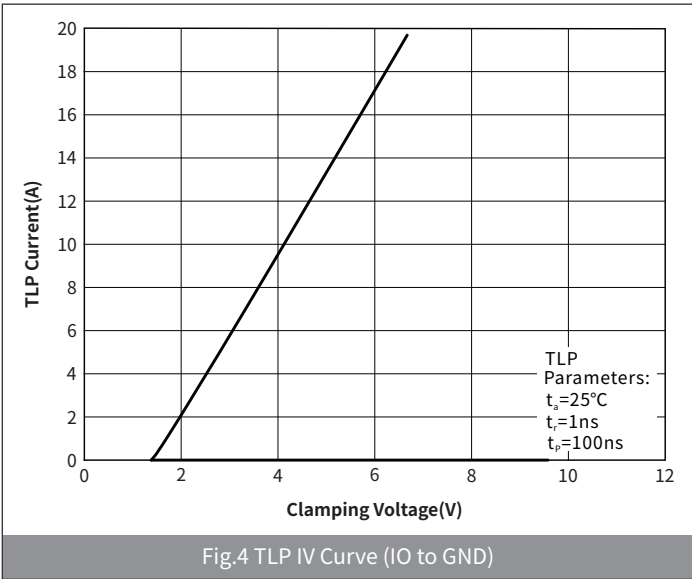
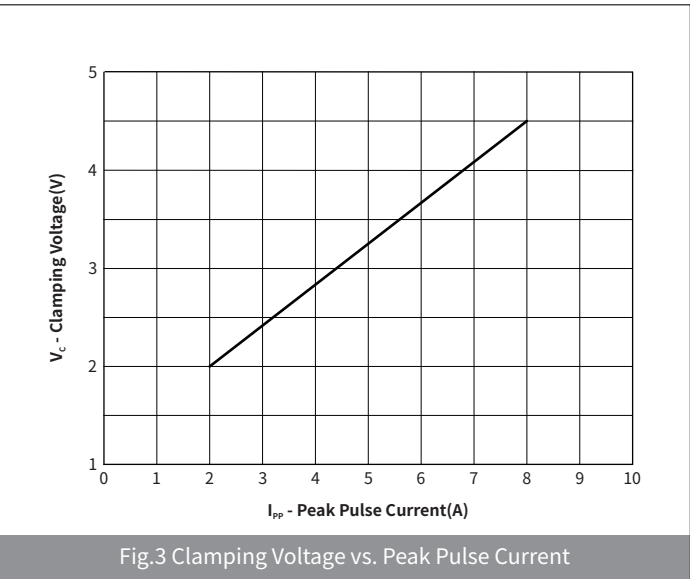
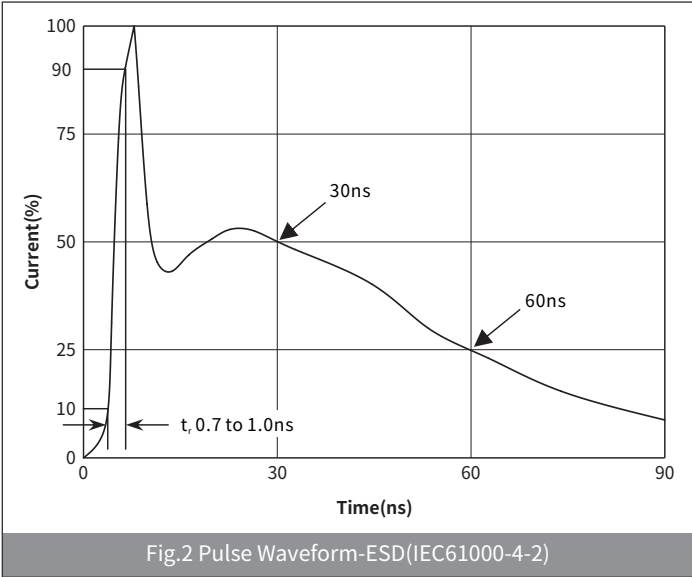
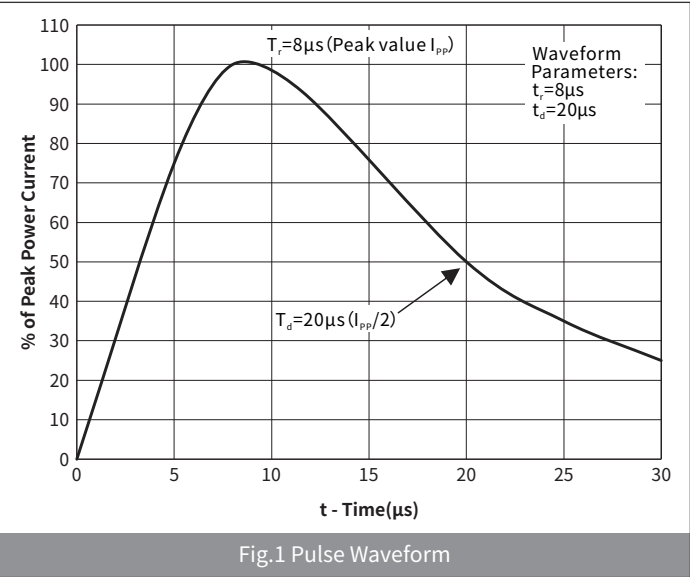
SYMBOL	PARAMETER
I _{PP}	Peak Pulse Current @8/20μs
V _C	Clamping Voltage @ I _{PP}
I _{BR} / I _T	Test Current
V _{BR}	Breakdown Voltage @ I _T
V _{RWM}	Peak Reverse Working Voltage
I _R	Reverse Leakage Current @ V _{RWM}
I _{TRIG}	Reverse Trigger Current
V _{TRIG}	Reverse Trigger Voltage
I _{HOLD}	Reverse Holding Current
V _{HOLD}	Reverse Holding Voltage
P _{PP}	Peak Pulse Power Dissipation



● Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	CONDITION	Min	Typ	Max	UNIT
Peak Reverse Working Voltage	V_{RWM}	$T_a=25^{\circ}\text{C}$	—	—	3.3	V
Breakdown Voltage	V_{BR}	$I_T=1\text{mA}, T_a=25^{\circ}\text{C}$	3.6	—	—	V
Reverse Leakage Current	I_R	$V_{RWM}=3.3\text{V}, T_a=25^{\circ}\text{C}$	—	—	0.1	μA
Dynamic Resistance	R_{DYN}	$Z_0=50\Omega$, calculated from 4A to 16A	—	0.25	—	Ω
TLP Clamping Voltage	$V_C@TLP$	$Z_0=50\Omega, T_p=100\text{ns}, T_r=1\text{ns}; TLP@16\text{A}$	—	5.5	—	V
Clamping Voltage	V_C	$I_{pp}=7.0\text{A}, t_p=8/20\mu\text{s}$	—	3.6	5.0	V
Junction Capacitance	C_J	$V_{RWM}=1.5\text{V}, f=1\text{MHz}$	—	0.4	0.5	pF

● Ratings And Characteristics Curves (Ta=25°C Unless otherwise specified)



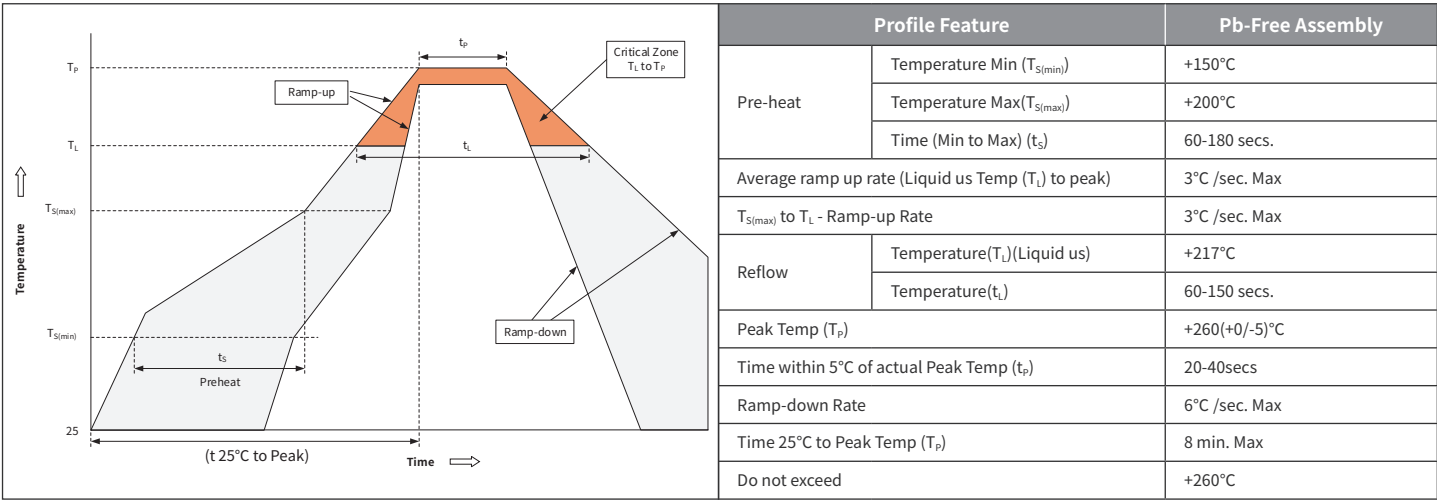
H3V3U25BS

Bi-directional 3.3V Ultra Small Capacitance ESD

Ordering Information

PREFERED P/N	PACKAGE	SIZE(mm)	DELIVERY MODE	MPQ(PCS)
H3V3U25BS	DFN2510	2.50×1.00×0.50	7" REEL	3,000

Recommended Soldering Conditions



Package Outline Dimensions (DFN2510)

